

## Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected Gate up to 2kV**
- **"Green" Device (Note 4)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering & Date Code Information: See Page 4
- Weight: 0.006 grams (approximate)

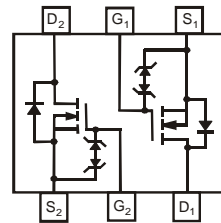


TOP VIEW



BOTTOM VIEW

SOT-563



TOP VIEW

Internal Schematic

## Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 8$	V
Drain Current (Note 1)	$I_D$	$T_A = 25^\circ\text{C}$ 540	mA
Steady State		$T_A = 85^\circ\text{C}$ 390	
Pulsed Drain Current (Note 3)	$I_{DM}$	1.5	A

## Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_d$	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_i, T_{STG}$	-65 to +150	$^\circ\text{C}$

## Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 10\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 1$	$\mu\text{A}$	$V_{GS} = \pm 4.5\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.4	0.55	$\Omega$	$V_{GS} = 4.5\text{V}, I_D = 540\text{mA}$
			0.5	0.70		$V_{GS} = 2.5\text{V}, I_D = 500\text{mA}$
			0.7	0.9		$V_{GS} = 1.8\text{V}, I_D = 350\text{mA}$
Forward Transfer Admittance	$ Y_{fs} $	200	—	—	ms	$V_{DS} = 10\text{V}, I_D = 0.2\text{A}$
Diode Forward Voltage (Note 5)	$V_{SD}$	0.5	—	1.4	V	$V_{GS} = 0\text{V}, I_S = 115\text{mA}$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	—	—	150	pF	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	$C_{OSS}$	—	—	25	pF	
Reverse Transfer Capacitance	$C_{RSS}$	—	—	20	pF	

- Notes:
1. Device mounted on FR-4 PCB.
  2. No purposefully added lead.
  3. Pulse width  $\leq 10\mu\text{s}$ , Duty Cycle  $\leq 1\%$ .
  4. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  5. Short duration pulse test used to minimize self-heating effect.

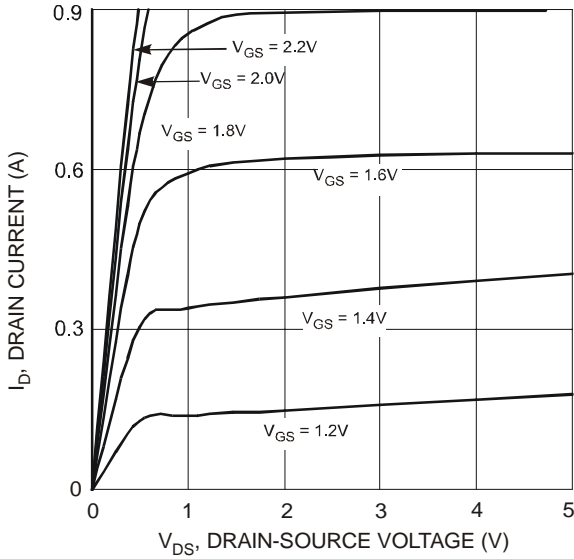


Fig. 1 Typical Output Characteristics

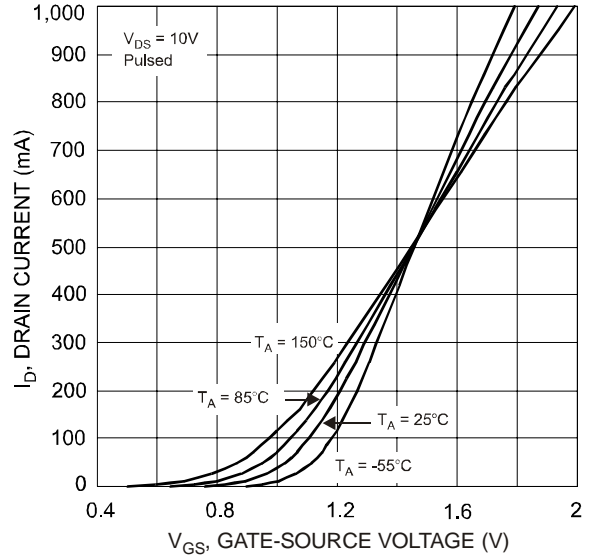


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

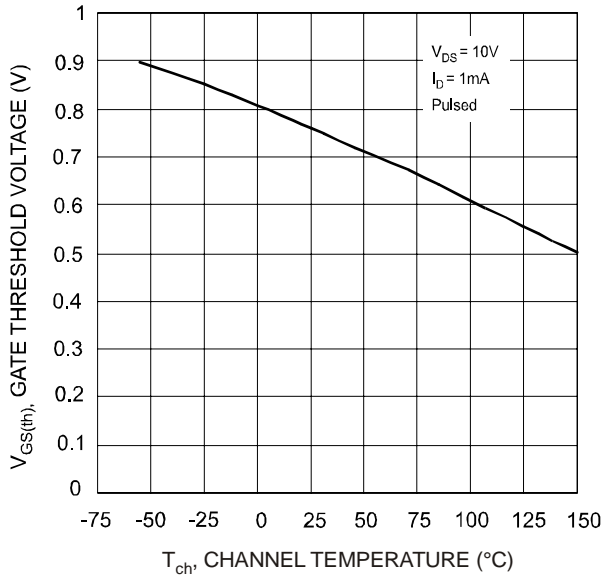


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

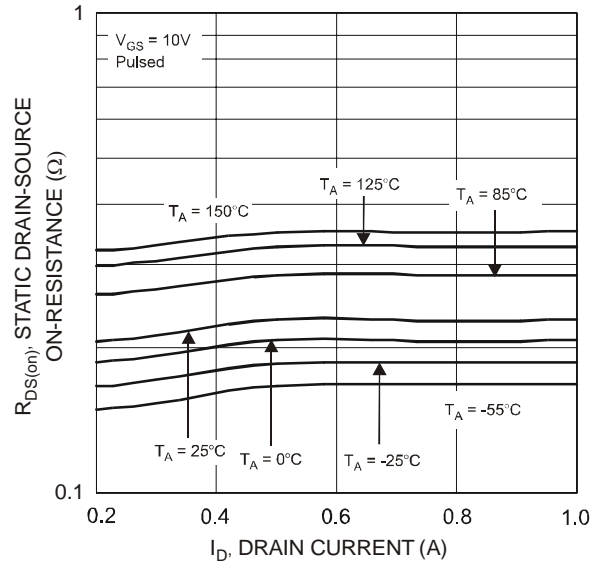


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

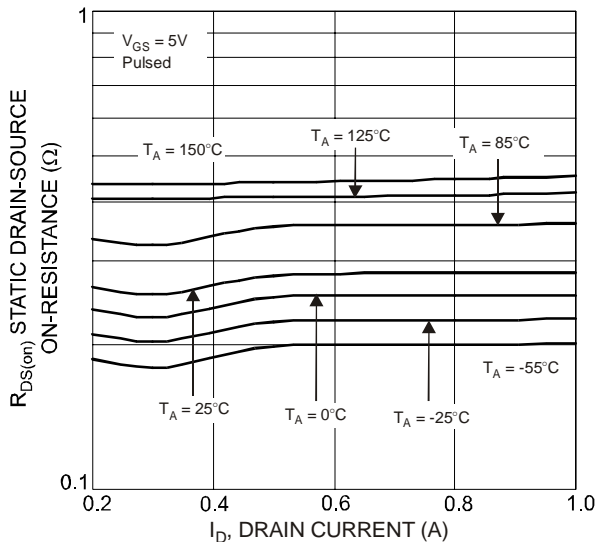


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

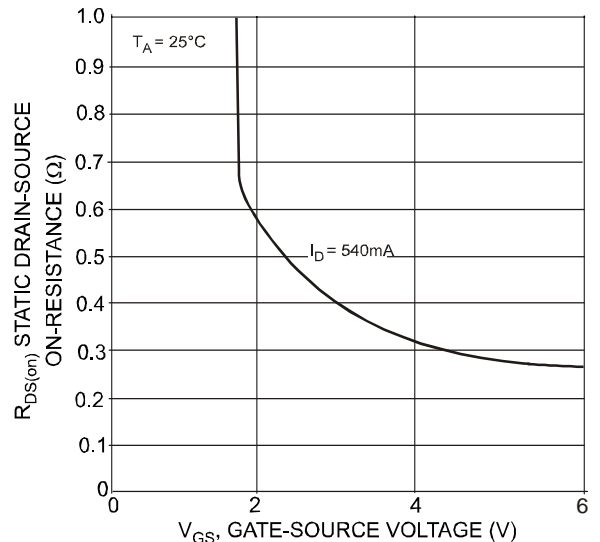


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage

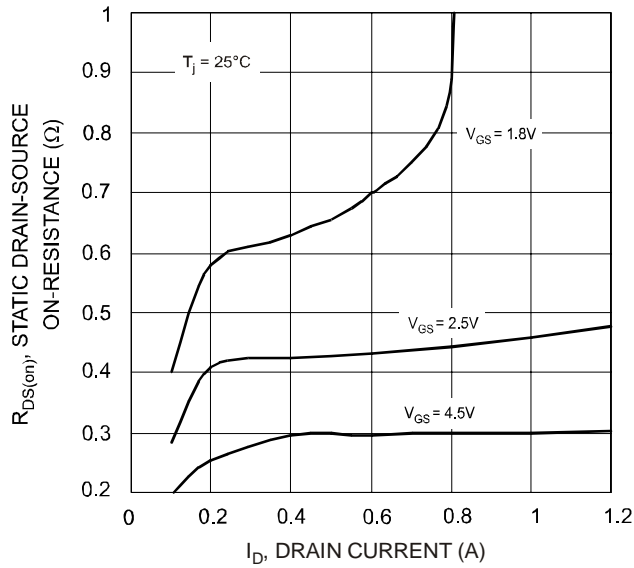


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage

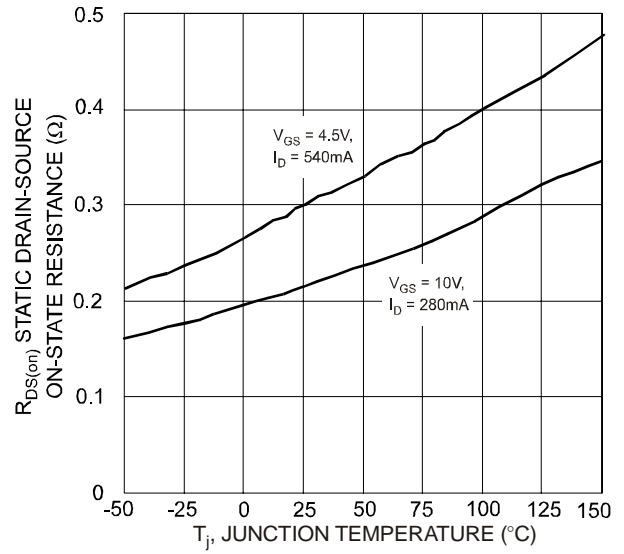


Fig. 8 Static Drain-Source, On-Resistance vs. Temperature

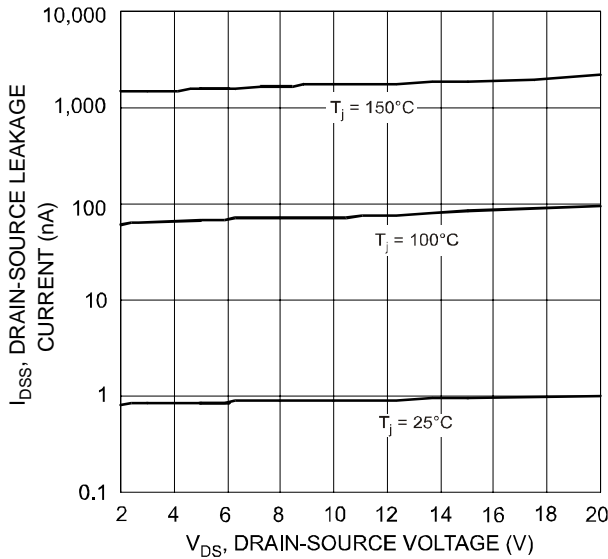


Fig. 9 Drain Source Leakage Current vs. Voltage

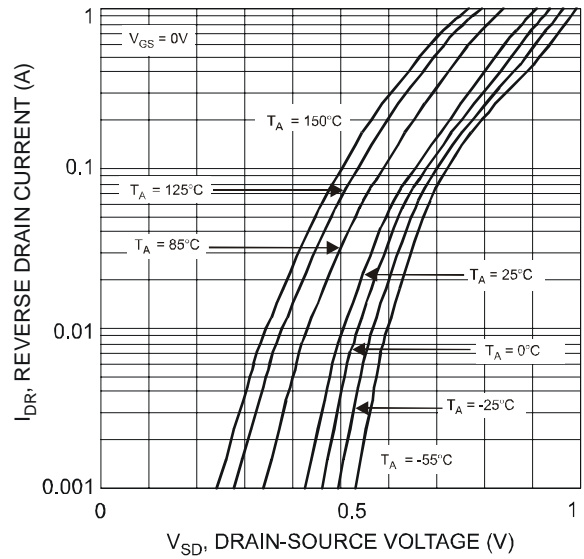


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage

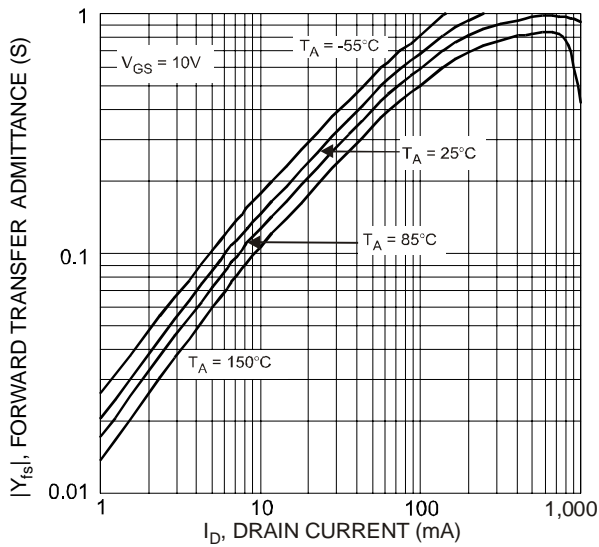


Fig. 11 Forward Transfer Admittance vs. Drain Current

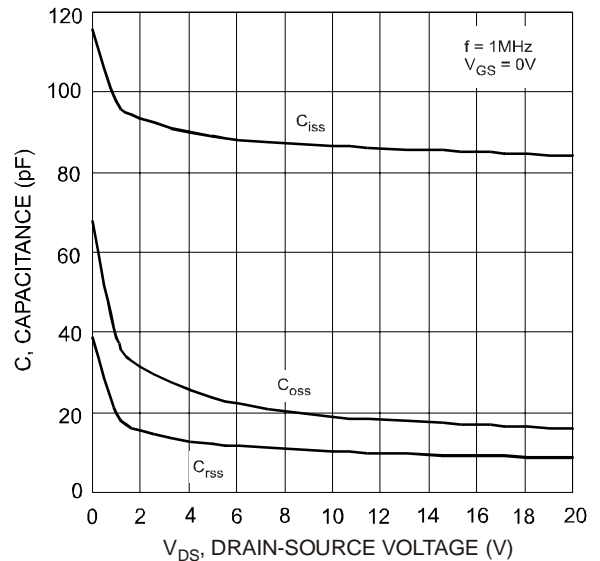


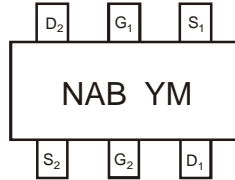
Fig. 12 Capacitance Variation

**Ordering Information** (Note 6)

Part Number	Case	Packaging
DMN2004VK-7	SOT-563	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**



NAB = Marking Code  
YM = Date Code Marking  
Y = Year ex: T = 2006  
M = Month ex: 9 = September

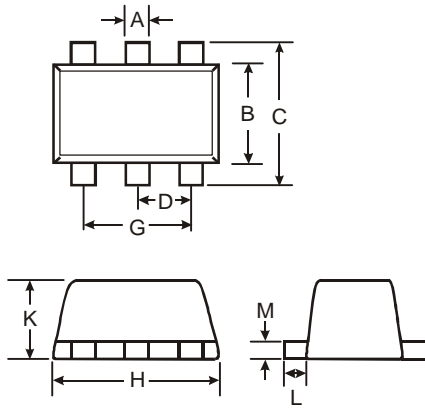
Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

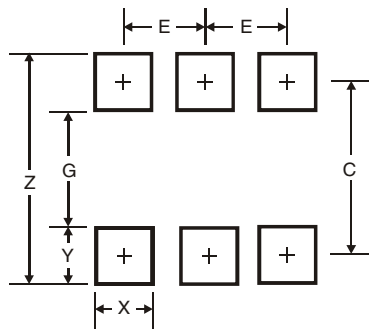
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C	1.7
E	0.5

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